



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

11 A

Features

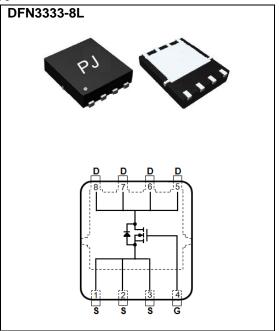
- R_{DS(ON)}, V_{GS}@10V, I_D@6A<72mΩ
- R_{DS(ON)}, V_{GS}@4.5V, I_D@3A<88mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	.,,	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current(Note 4)	Tc=25°C	- I _D	11		
	T _C =100°C		7	Α	
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	44		
Power Dissipation	T _C =25°C	Po	20	10/	
	Tc=100°C		8	W	
Continuous Drain Current(Note 4)	T _A =25°C	l _D	3.7	^	
	T _A =70°C		2.9	Α	
Power Dissipation	T _A =25°C	,	2	W	
	T _A =70°C	Pb	1.3		
Single Pulse Avalanche Energy ^(Note 6)		Eas	25	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R ₀ JC	6.3	°C/W	
	Junction to Ambient	R _{θJA}	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA V _{DS} =V _{GS} , I _D =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$		1	1.8	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =6A	-	53	72	mΩ
		V _{GS} =4.5V, I _D =3A	-	61	88	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic ^(Note 7)						
Total Gate Charge	Q_g	V _{DS} =48V, I _D =6A, V _{GS} =10V ^(Note 1,2)	-	9.3	-	nC
Gate-Source Charge	Q_{gs}		-	2.2	-	
Gate-Drain Charge	Q_gd		-	1.9	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V,	-	509	-	pF
Output Capacitance	Coss		-	47	-	
Reverse Transfer Capacitance	Crss	I = I IVII IZ	-	23	-	
Turn-On Delay Time	td _(on)	\\\\ 20\\\ I 4A	-	3.2	-	
Turn-On Rise Time	tr	$V_{DD}=30V, I_{D}=1A,$ $V_{GS}=10V,$ $R_{G}=3.3\Omega^{(Note 1,2)}$	-	9.7	-	ns
Turn-Off Delay Time	td _(off)		-	18.5	-	
Turn-Off Fall Time	t _f	NG=3.312(*******)=/	-	6.4	-	
Drain-Source Diode			_			
Maximum Continuous Drain-Source	la.		-	-	11	А
Diode Forward Current	I _S					
Reverse Recovery Time	V_{SD}	I _S =1A, V _{GS} =0V	-	0.75	1	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=1mH, I_{AS} =7A, V_{DD} =25V, V_{GS} =10V, Starting T_{J} =25°C.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

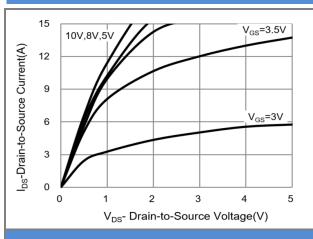


Fig.1 On-Region Characteristics

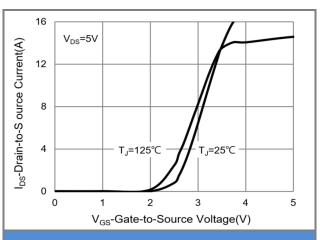


Fig.2 Transfer Characteristics

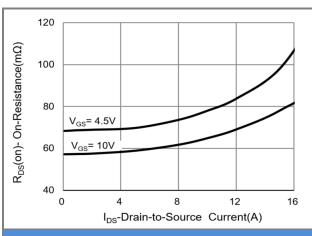


Fig.3 On-Resistance vs. Drain Current

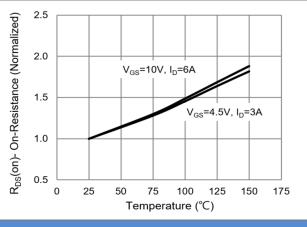


Fig.4 On-Resistance vs. Junction temperature

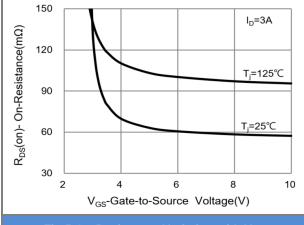


Fig.5 On-Resistance Variation with V_{GS}

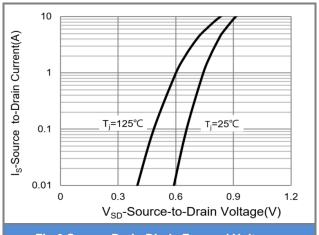


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

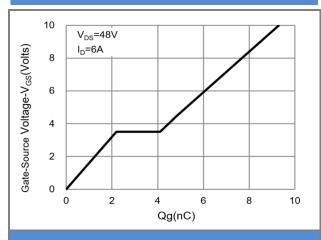


Fig.7 Gate-Charge Characteristics

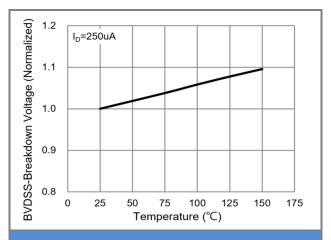


Fig.8 Breakdown Voltage Variation vs. Temperature

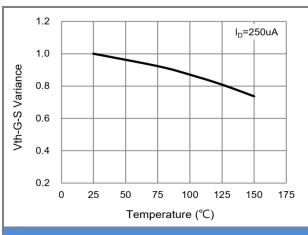


Fig.9 Threshold Voltage Variation with Temperature

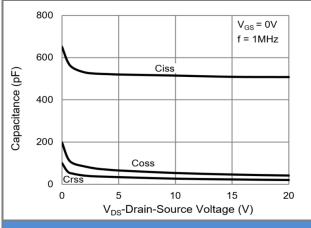
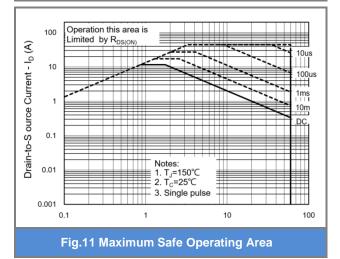


Fig.10 Capacitance vs. Drain-Source Voltage



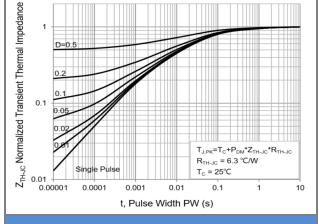


Fig.12 Normalized Transient Thermal Impedance

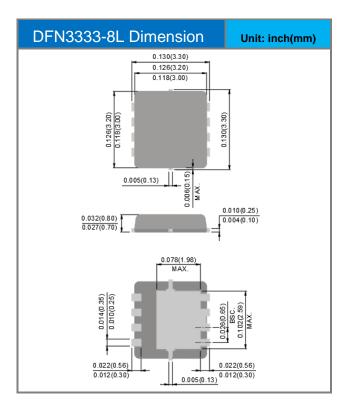


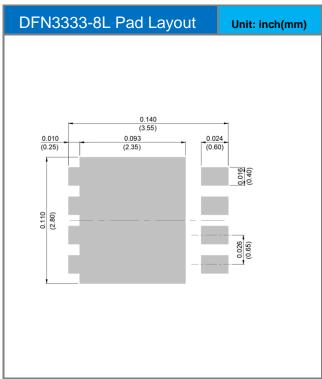


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4460AP_R2_00001	DFN3333-8L	5K pcs / 13" reel	4460	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout









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